

Silicon NPN Power Transistors

2SC1309

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For TV vertical deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

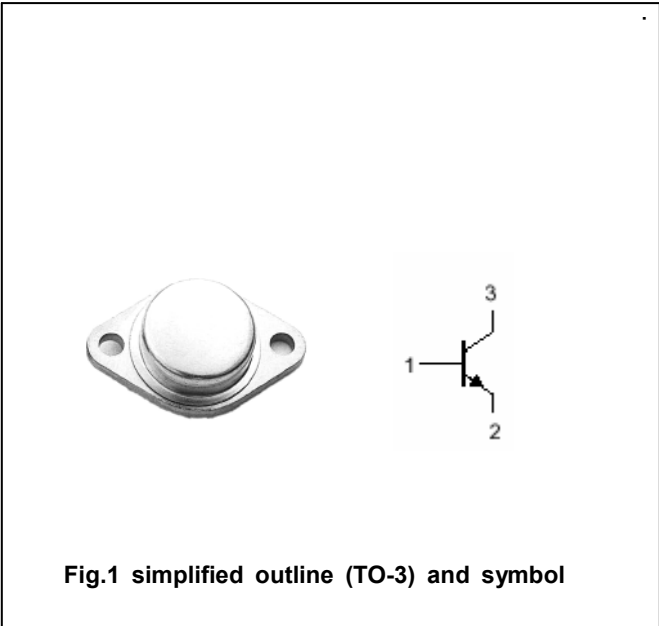


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1200	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
P _T	Total power dissipation	T _C =25□	80	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1.0mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5 A; I _B =1.2 A			10	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5 A; I _B =1.2 A			2	V
I _{CBO}	Collector cut-off current	V _{CB} =1200V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =10V	10			

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PACKAGE OUTLINE

